Z0109MA

4Q Triac

17 September 2018

Product data sheet

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring direct interfacing to logic ICs and low power gate drivers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Triggering in all four quadrants

3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

4. Quick reference data

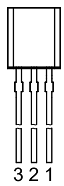
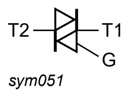
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 45$ °C; Fig. 1; Fig. 2; Fig. 3		-	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5		-	-	8	A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms		-	-	8.5	A
T_j	junction temperature			-	-	125	°C
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12$ V; $I_T = 0.1$ A; T2+ G+; $T_j = 25$ °C; Fig. 7		-	-	10	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2+ G-; $T_j = 25$ °C; Fig. 7		-	-	10	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2- G-; $T_j = 25$ °C; Fig. 7		-	-	10	mA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		V_D = 12 V; I_T = 0.1 A; T2- G+; T_j = 25 °C; Fig. 7		-	-	10	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	10	mA
V_T	on-state voltage	I_T = 1 A; T_j = 25 °C; Fig. 10		-	1.3	1.6	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12		50	-	-	V/μs
dV_{com}/dt	rate of change of commutating voltage	V_D = 400 V; T_j = 110 °C; dI_{com}/dt = 0.44 A/ms; I_T = 1 A; gate open circuit		2	-	-	V/μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2	 TO-92 (SOT54)	
2	G	gate		
3	T1	main terminal 1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
Z0109MA	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq$ 45 °C; Fig. 1; Fig. 2; Fig. 3		-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5		-	8	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms		-	8.5	A
I^2t	I^2t for fusing	t_p = 10 ms; SIN		-	0.32	A²s
dI_T/dt	rate of rise of on-state current	I_G = 20 mA; T2+ G+		-	50	A/µs
		I_G = 20 mA; T2+ G-		-	50	A/µs
		I_G = 20 mA; T2- G-		-	50	A/µs
		I_G = 20 mA; T2- G+		-	20	A/µs
I_{GM}	peak gate current			-	1	A
P_{GM}	peak gate power			-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period		-	0.1	W
T_{stg}	storage temperature			-40	150	°C
T_j	junction temperature			-	125	°C

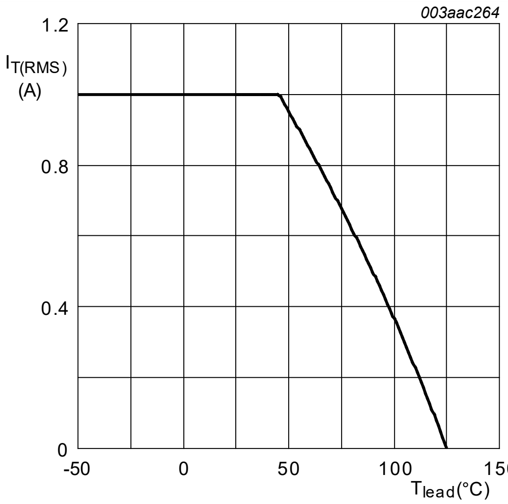
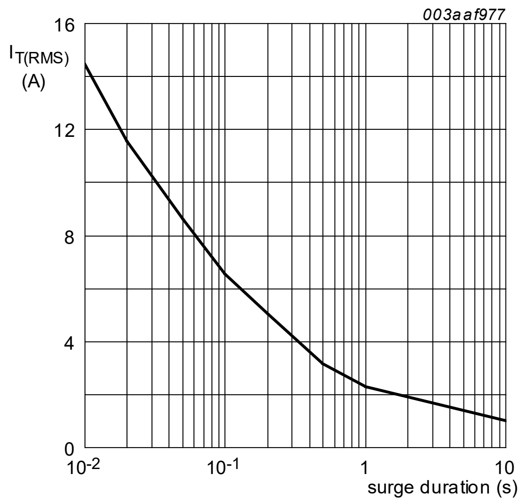
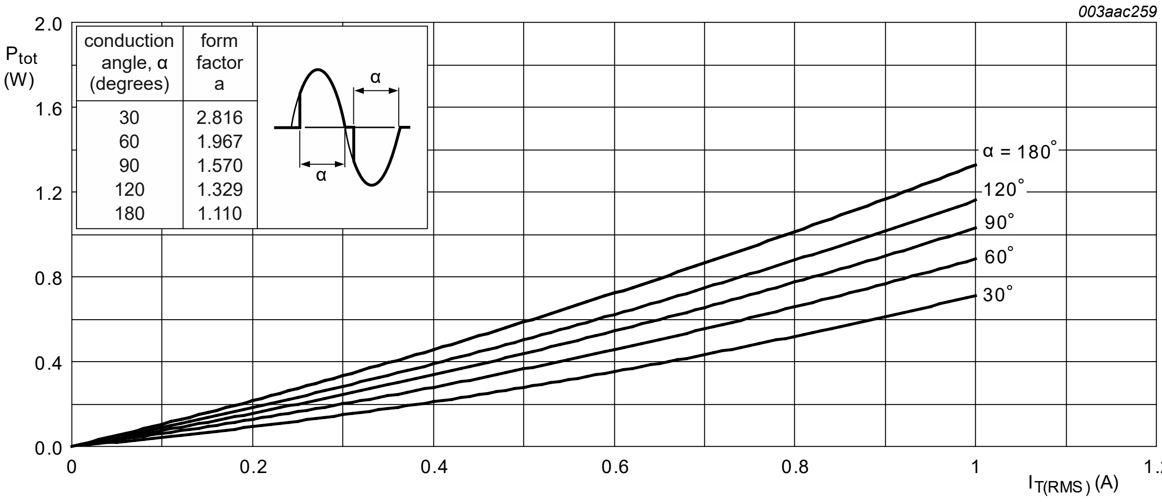


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz; T_{lead} = 45 °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values

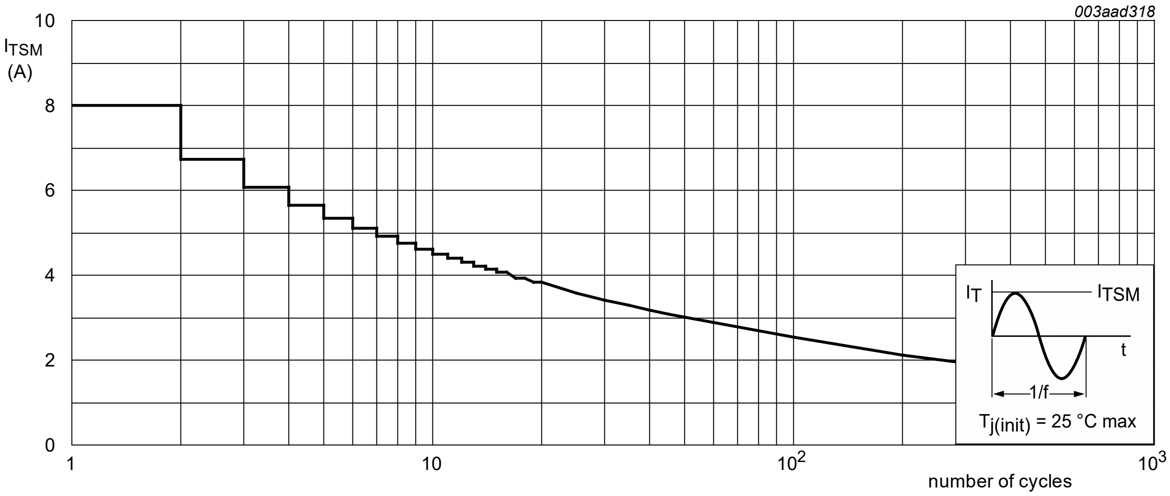


conduction angle, α (degrees)	form factor a
30	2.816
60	1.967
90	1.570
120	1.329
180	1.110

α = conduction angle

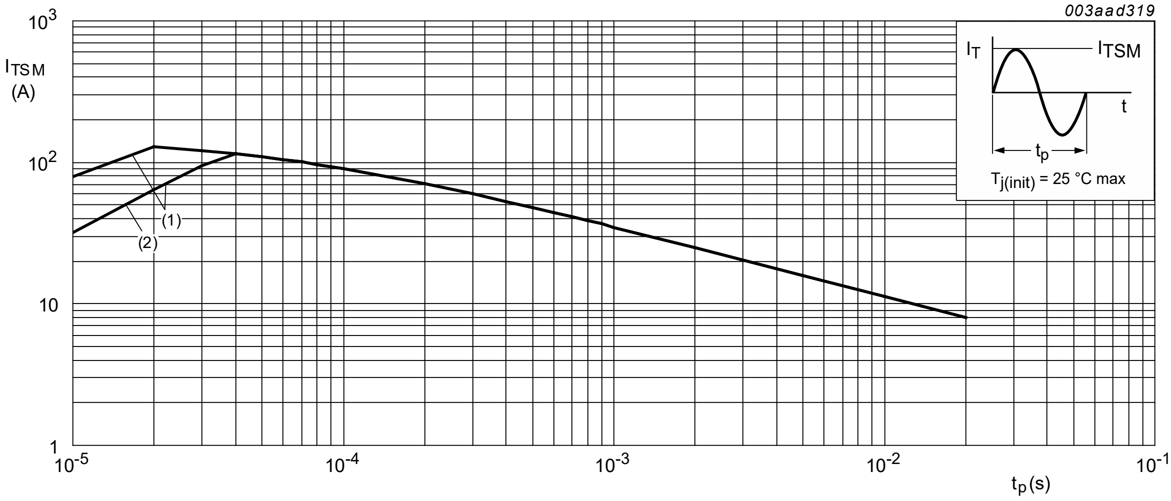
a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



t_p ≤ 20 ms
(1) dI_T/dt limit
(2) T2- G+ quadrant limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; Fig. 6		-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	full cycle; printed-circuit board mounted; lead length = 4 mm		-	150	-	K/W

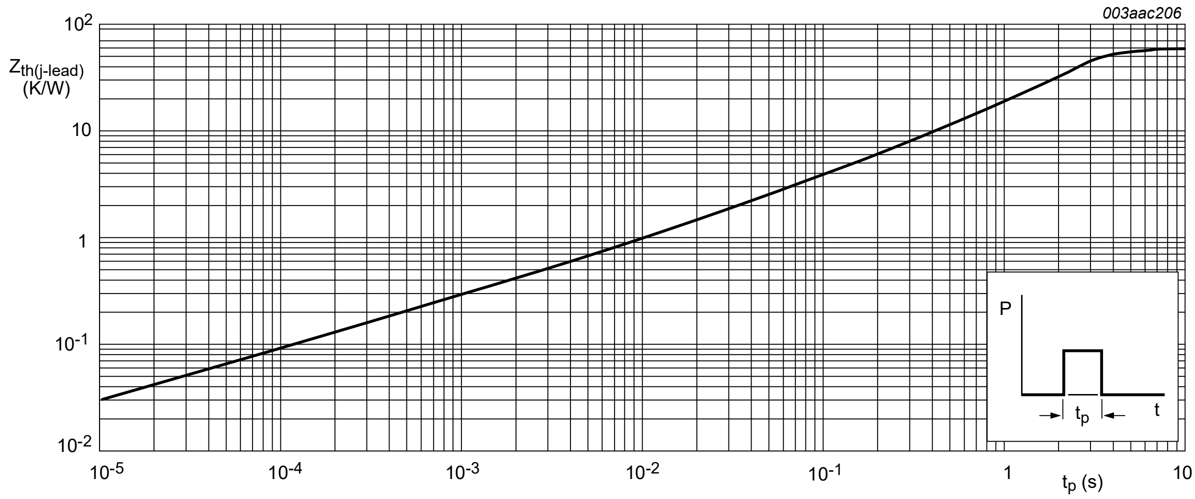
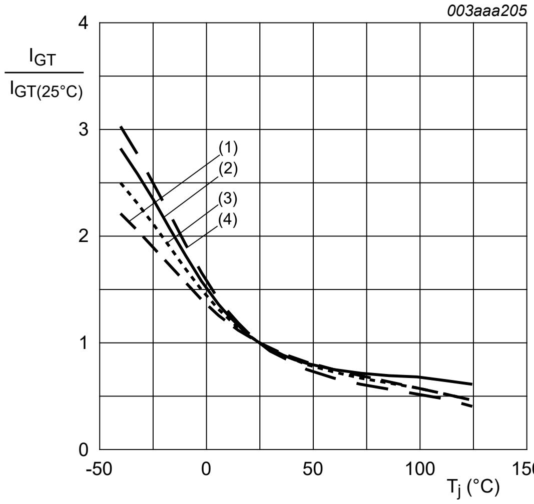


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		-	-	10	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		-	-	10	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		-	-	10	mA
		V_D = 12 V; I_T = 0.1 A; T2- G+; T_j = 25 °C; Fig. 7		-	-	10	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 8		-	-	15	mA
		V_D = 12 V; I_G = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 8		-	-	25	mA
		V_D = 12 V; I_G = 0.1 A; T2- G-; T_j = 25 °C; Fig. 8		-	-	15	mA
		V_D = 12 V; I_G = 0.1 A; T2- G+; T_j = 25 °C; Fig. 8		-	-	15	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	10	mA
V_T	on-state voltage	I_T = 1 A; T_j = 25 °C; Fig. 10		-	1.3	1.6	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C		-	-	1	V
		V_D = 600 V; I_T = 0.1 A; T_j = 125 °C; Fig. 11		0.2	-	-	V
I_D	off-state current	V_D = 600 V; T_j = 125 °C		-	-	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 12		50	-	-	V/µs
dV_{com}/dt	rate of change of commutating voltage	V_D = 400 V; T_j = 110 °C; dI_{com}/dt = 0.44 A/ms; I_T = 1 A; gate open circuit		2	-	-	V/µs



(1) T2- G+
(2) T2- G-
(3) T2+ G-
(4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

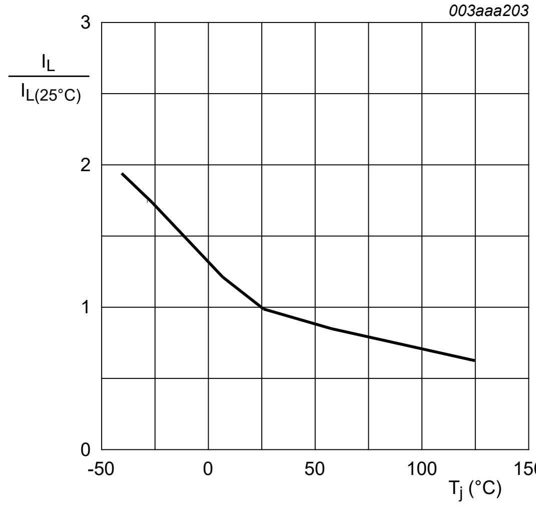


Fig. 8. Normalized latching current as a function of junction temperature

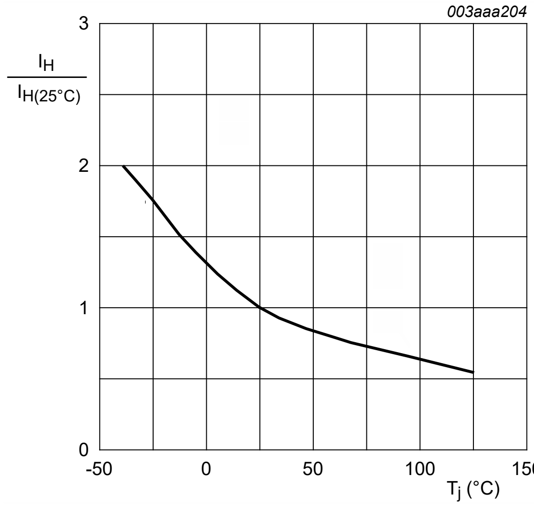
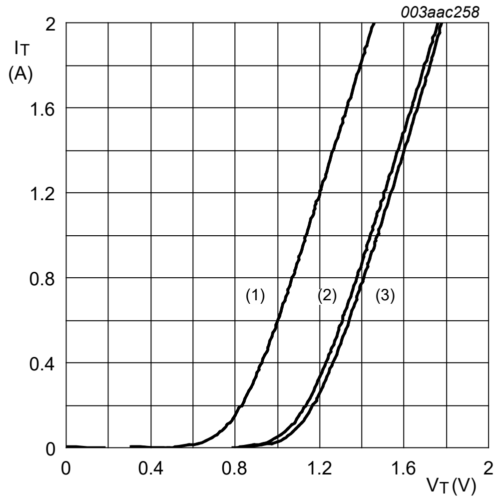


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 1.13 V
R_s = 0.31 Ω
(1) T_j = 125 °C; typical values
(2) T_j = 125 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

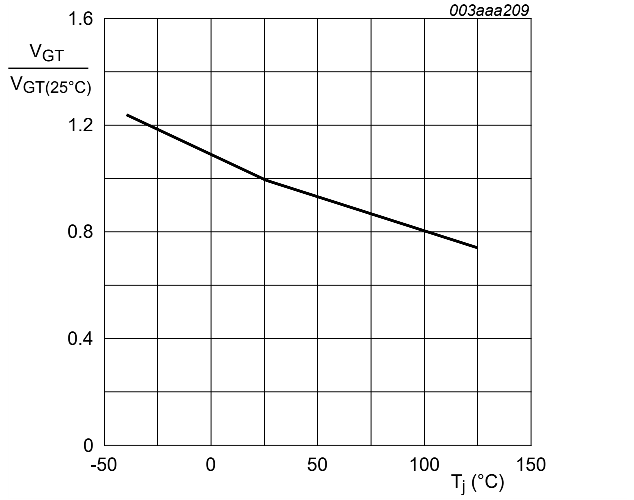
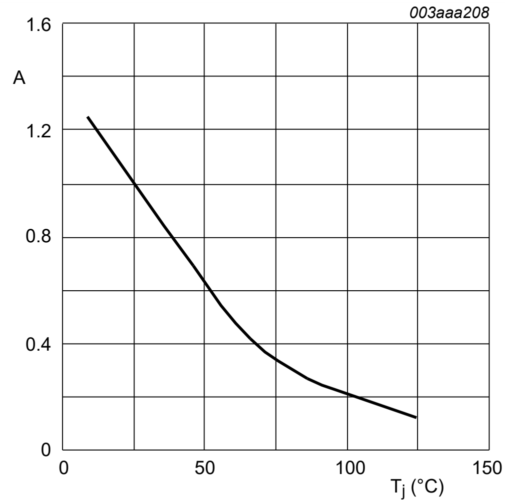


Fig. 11. Normalized gate trigger voltage as a function of junction temperature



$$A = \frac{dV_{D(Tj\,°\,C)} / dt}{dV_{D(25\,°\,C)} / dt}$$

Fig. 12. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

10. Package outline

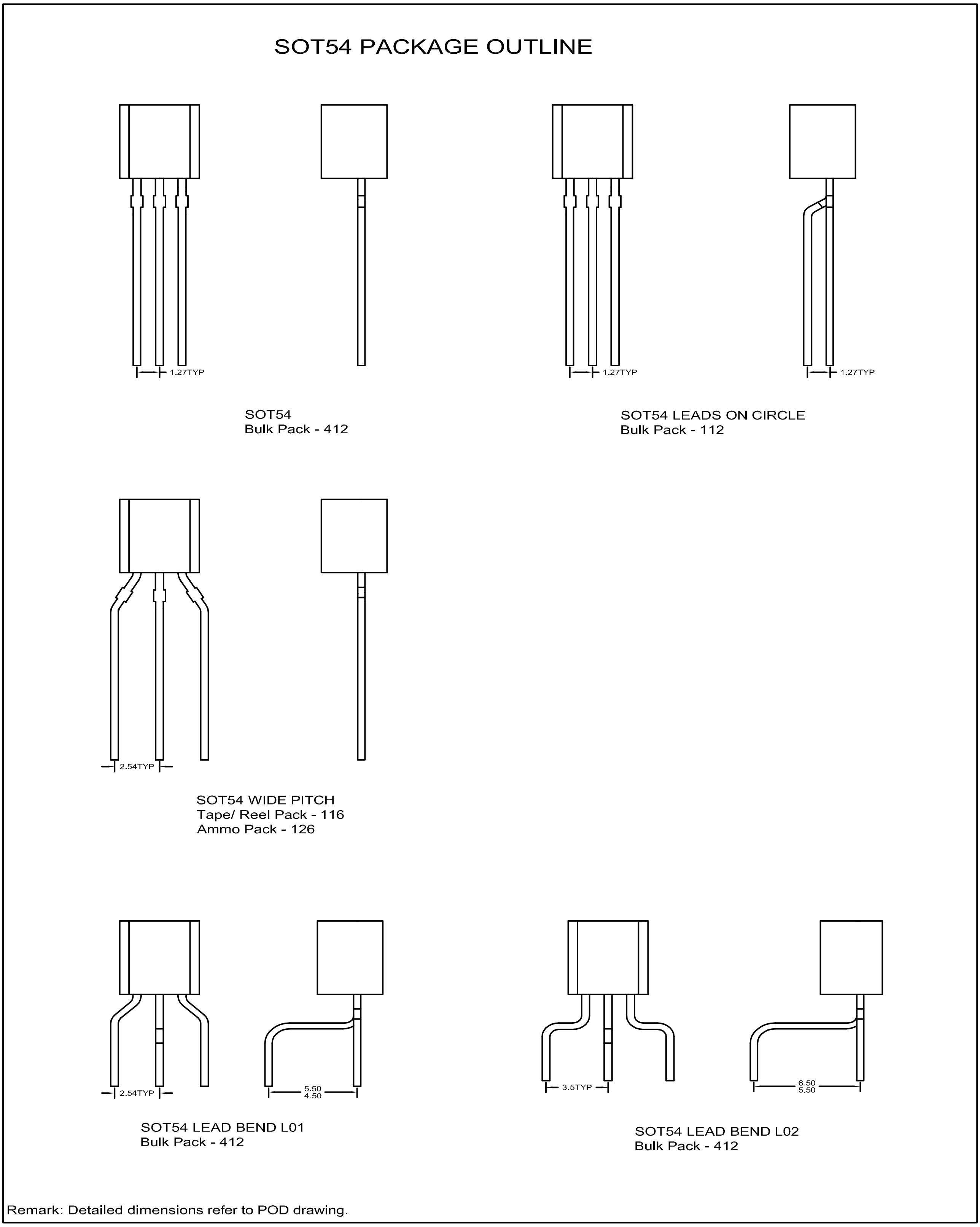


Fig. 13. Package outline TO-92 (SOT54)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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12. Contents

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